

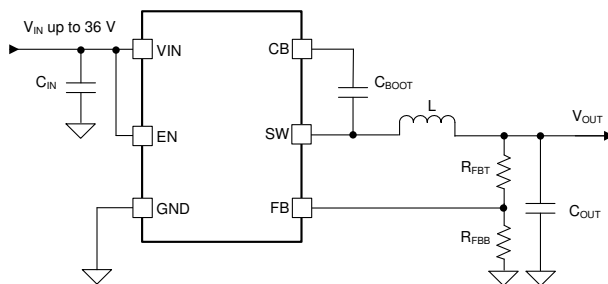
## LV3842 4V~36V、600mA、同期整流降圧型コンバータ

### 1 特長

- 新製品を利用可能:
  - LMR54406 4V~45V、0.6A、1.1MHz 同期整流降圧コンバータ
- 市場投入の迅速化:
  - TPSM365R6 3V~65V、0.6A、200kHz~2.2MHz 電源モジュール
- 堅牢な産業用アプリケーション向けの構成
  - 40V の絶対最大定格に対応する 4V~36V の入力電圧範囲
  - 600mA の連続出力電流
  - 70ns の最小スイッチ・オン時間
  - 98% の最大デューティ・サイクル
  - PFM および強制 PWM (FPWM) オプション
  - 1.1MHz のスイッチング周波数
  - あらかじめ出力にバイアスが印加された状態でのスタートアップをサポート
  - ヒックアップ・モードによる短絡保護
  - 25°C の接合部温度で許容誤差  $\pm 0.5\%$  の基準電圧
  - 高精度のイネーブル
  - 過熱保護
- 小型のソリューションと使いやすさ
  - 同期整流器内蔵
  - 使いやすさを実現した内部補償
  - SOT-23-6 パッケージ

### 2 アプリケーション

- 電気メーター
- スマート・メーター・データ・コレクタ、コンセントレータ
- 電力線通信 (PLC) モジュール
- $V_{IN}$  が広い汎用電源



代表的なアプリケーション回路図

### 3 概要

LV3842 は使いやすい同期整流降圧 DC/DC コンバータで、最大 600mA の負荷電流を駆動できます。このデバイスは、4V~36V の広い入力電圧範囲で動作し、レギュレートされていない電源からの電源調整を行うさまざまな産業用アプリケーションに適しています。

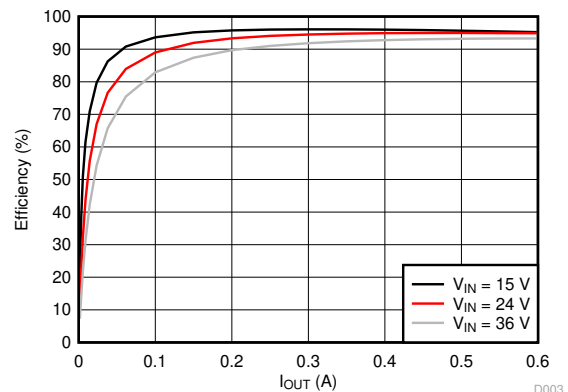
LV3842 は 1.1MHz のスイッチング周波数を採用しているため、ソリューションを小型化できます。また、LV3842 には FPWM (強制 PWM) バージョンがあり、一定の周波数を維持しながら、負荷範囲の全体にわたって出力電圧リップルを小さくできます。ソフトスタートと補償回路が内部に採用されており、最小限の外付け部品のみでデバイスを使用できます。

このデバイスには、サイクル単位の電流制限、ヒックアップ・モード短絡保護、過剰な電力消費時のサーマル・シャットダウンなどの保護機能が組み込まれています。LV3842 は、SOT-23-6 パッケージで供給されます。

#### パッケージ情報

部品番号	パッケージ (1)	パッケージ・サイズ (2)
LV3842	DBV (SOT-23, 6)	2.90mm × 2.80mm

- (1) 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
- (2) パッケージ・サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



効率と出力電流との関係  $V_{OUT} = 12V$ 、1.1MHz、FPWM



## Table of Contents

<b>1 特長</b> .....	1	8.3 Feature Description.....	11
<b>2 アプリケーション</b> .....	1	8.4 Device Functional Modes.....	15
<b>3 概要</b> .....	1	<b>9 Application and Implementation</b> .....	16
<b>4 Revision History</b> .....	2	9.1 Application Information.....	16
<b>5 Device Comparison Table</b> .....	3	9.2 Typical Application.....	16
<b>6 Pin Configuration and Functions</b> .....	4	9.3 Power Supply Recommendations.....	21
<b>7 Specifications</b> .....	5	9.4 Layout.....	21
7.1 Absolute Maximum Ratings.....	5	<b>10 Device and Documentation Support</b> .....	23
7.2 ESD Ratings.....	5	10.1 Documentation Support.....	23
7.3 Recommended Operating Conditions.....	5	10.2 ドキュメントの更新通知を受け取る方法.....	23
7.4 Thermal Information.....	5	10.3 サポート・リソース.....	23
7.5 Electrical Characteristics.....	6	10.4 Trademarks.....	23
7.6 Timing Requirements.....	7	10.5 静電気放電に関する注意事項.....	23
7.7 Switching Characteristics.....	7	10.6 用語集.....	23
7.8 Typical Characteristics.....	8	<b>11 Mechanical, Packaging, and Orderable Information</b> .....	24
<b>8 Detailed Description</b> .....	10	11.1 Tape and Reel Information.....	24
8.1 Overview.....	10		
8.2 Functional Block Diagram.....	10		

## 4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

<b>Changes from Revision B (January 2019) to Revision C (August 2023)</b>	<b>Page</b>
• 文書全体にわたって表、図、相互参照の採番方法を更新.....	1
• LMR54406 および TPSM365R6 へのリンクを追加.....	1
• 最初の公開リリース.....	1
• 電流規格を満たすよう「パッケージ情報」表を更新.....	1
• Updated <i>ESD Ratings</i> table to meet current standards.....	5
<b>Changes from Revision A (August 2018) to Revision B (January 2019)</b>	<b>Page</b>
• LV3842XDBVT および LV3842XDBVR のデバイス・マーキングを変更.....	1
<b>Changes from Revision * (May 2018) to Revision A (August 2018)</b>	<b>Page</b>
• 「機能説明」セクション、「代表的特性」セクション、「詳細説明」セクション、「メカニカル、パッケージ、および注文情報」セクションの PFM バージョン情報を追加.....	1
• Added the Device Comparison Table.....	3
• Added $I_Q$ , $I_{LS\_ZC}$ value for PFM version.....	6

## 5 Device Comparison Table

PART NUMBER	Frequency	PFM or FPWM	Output
LV3842XF	1.1 MHz	FPWM	Adjustable
LV3842X	1.1 MHz	PFM	Adjustable

## 6 Pin Configuration and Functions

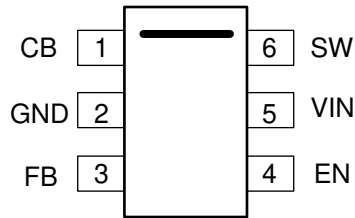


图 6-1. DBV Package 6-Pin SOT-23-6 Top View

表 6-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NO.	NAME		
1	CB	P	Bootstrap capacitor connection for high-side FET driver. Connect a high quality 100 nF capacitor from this pin to the SW pin.
2	GND	G	Power ground terminal, connected to the source of low-side FET internally. Connect to system ground, ground side of $C_{IN}$ and $C_{OUT}$ . Path to $C_{IN}$ must be as short as possible.
3	FB	A	Feedback input to the convertor. Connect a resistor divider to set the output voltage. Never short this terminal to ground during operation.
4	EN	A	Precision enable input to the convertor. Do not float. High = on, Low = off. Can be tied to VIN. Precision enable input allows adjustable UVLO by external resistor divider.
5	VIN	P	Supply input terminal to internal bias LDO and high-side FET. Connect to input supply and input bypass capacitors $C_{IN}$ . Input bypass capacitors must be directly connected to this pin and GND.
6	SW	P	Switching output of the convertor. Internally connected to source of the high-side FET and drain of the low-side FET. Connect to power inductor.

(1) A = Analog, P = Power, G = Ground.

## 7 Specifications

### 7.1 Absolute Maximum Ratings

Over the recommended operating junction temperature range of -40 °C to 125 °C (unless otherwise noted) <sup>(1)</sup>

PARAMETER		MIN	MAX	UNIT
Input Voltages	V <sub>IN</sub> to GND	-0.3	40	V
	EN to GND	-0.3	V <sub>IN</sub> + 0.3	
	FB to GND	-0.3	5.5	
Output Voltages	SW to GND	-0.3	V <sub>IN</sub> + 0.3	V
	SW to GND less than 10 ns transient	-3.5	40	
	CB to SW	-0.3	5.5	
T <sub>J</sub>	Junction temperature <sup>(2)</sup>	-40	150	°C
T <sub>stg</sub>	Storage temperature	-65	150	

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Operating at junction temperatures greater than 125°C, although possible, degrades the lifetime of the device.

### 7.2 ESD Ratings

PARAMETER	DEFINITION		VALUE	UNIT
V <sub>ESD</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	± 2500	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	± 750	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 7.3 Recommended Operating Conditions

Over the recommended operating junction temperature range of -40 °C to 125 °C (unless otherwise noted) <sup>(1)</sup>

PARAMETER		MIN	MAX	UNIT
Input Voltages	V <sub>IN</sub> to GND	4	36	V
	EN	0	V <sub>IN</sub>	
	FB	0	4.5	
Output Voltage	V <sub>OUT</sub>	1.0	95% of V <sub>IN</sub>	V
Output Current	I <sub>OUT</sub>	0	600	mA
Temperature	Operating junction temperature range, T <sub>J</sub>	-40	+125	°C

- (1) *Recommended Operating Conditions* indicate conditions for which the device is intended to be functional, but do not verify specific performance limits. For verified specifications, see *Electrical Characteristics*.

### 7.4 Thermal Information

THERMAL METRIC <sup>(1) (2)</sup>		DBV (6 PINS)	UNIT
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	173	°C/W
R <sub>θJC_T</sub>	Junction-to-case (TOP) thermal resistance	116	°C/W
R <sub>θJC_B</sub>	Junction-to-case (BOTTOM) thermal resistance	31	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	20	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	30	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#)

- (2) The value of  $R_{\theta JA}$  given in this table is only valid for comparison with other packages and can not be used for design purposes. These values were calculated in accordance with JESD 51-7, and simulated on a specified JEDEC board. They do not represent the performance obtained in an actual application

## 7.5 Electrical Characteristics

Limits apply over the recommended operating junction temperature ( $T_J$ ) range of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ , unless otherwise stated. Minimum and maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at  $T_J = 25^{\circ}\text{C}$ , and are provided for reference purposes only. Unless otherwise stated, the following conditions apply:  $V_{IN} = 4\text{ V}$  to  $36\text{ V}$ .

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SUPPLY VOLTAGE (VIN PIN)</b>						
$V_{IN}$	Operation input voltage		4		36	V
$V_{IN\_UVLO}$	Undervoltage lockout thresholds	Rising threshold	3.55	3.75	4.00	V
		Falling threshold	3.25	3.45	3.65	
		Hysteresis		0.3		
$I_Q$	Operating quiescent current (non-switching)	PFM version, $V_{EN} = 3.3\text{ V}$ , $V_{FB} = 1.1\text{ V}$		80	120	$\mu\text{A}$
$I_{SHDN}$	Shutdown current			3	10	$\mu\text{A}$
<b>ENABLE (EN PIN)</b>						
$V_{EN\_H}$	Enable rising threshold voltage		1.1	1.23	1.36	V
$V_{EN\_L}$	Enable falling threshold voltage		0.95	1.1	1.22	V
$V_{EN\_HYS}$	Enable hysteresis voltage			0.13		V
$I_{EN}$	Leakage current at EN pin	$V_{EN} = 3.3\text{ V}$		10	200	nA
<b>VOLTAGE REFERENCE (FB PIN)</b>						
$V_{REF}$	Reference voltage	$T_J = 25^{\circ}\text{C}$	0.995	1.00	1.005	V
		$T_J = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$	0.98	1.00	1.02	V
$I_{FB}$	Leakage current at FB pin	$V_{FB} = 1.2\text{ V}$		0.2	50	nA
<b>CURRENT LIMITS AND HICCUP</b>						
$I_{HS\_LIMIT}$	Peak inductor current limit			1.1		A
$I_{LS\_LIMIT}$	Valley inductor current limit			0.8		A
$I_{LS\_ZC}$	Zero cross current (PFM version)			20		mA
$I_{LS\_NEG}$	Negative current limit (FPWM version)			-0.5		A
$V_{HICCUP}$	Hiccup threshold of FB pin	% of reference voltage		40%		
<b>INTEGRATED MOSFETS</b>						
$R_{DS\_ON\_HS}$	High-side MOSFET ON-resistance	$T_J = 25^{\circ}\text{C}$		550		m $\Omega$
$R_{DS\_ON\_LS}$	Low-side MOSFET ON-resistance	$T_J = 25^{\circ}\text{C}$		285		m $\Omega$
<b>THERMAL SHUTDOWN (1)</b>						
$T_{SHDN}$	Thermal shutdown threshold			170		$^{\circ}\text{C}$
$T_{HYS}$	Hysteresis			12		$^{\circ}\text{C}$

- (1) Specified by design.

## 7.6 Timing Requirements

Limits apply over the recommended operating junction temperature ( $T_J$ ) range of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ , unless otherwise stated. Minimum and maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at  $T_J = 25^{\circ}\text{C}$ , and are provided for reference purposes only. Unless otherwise stated, the following conditions apply:  $V_{IN} = 4\text{ V}$  to  $36\text{ V}$ .

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SOFT START</b>						
$t_{SS}$	Internal soft-start time	The time of internal reference to increase from 10% to 90% of $V_{REF}$ , $V_{IN} = 12\text{ V}$		1.8		ms
<b>HICCUP Protection</b>						
$T_{HICCUP}$	Hiccup time	$V_{IN} = 12\text{ V}$		135		ms

## 7.7 Switching Characteristics

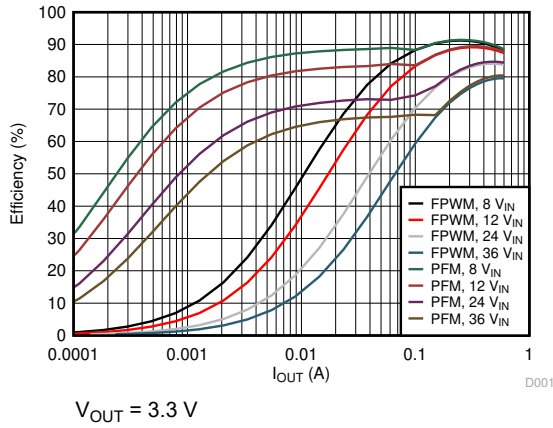
Limits apply over the recommended operating junction temperature ( $T_J$ ) range of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ , unless otherwise stated. Minimum and maximum limits are specified through test, design or statistical correlation. Typical values represent the most likely parametric norm at  $T_J = 25^{\circ}\text{C}$ , and are provided for reference purposes only. Unless otherwise stated, the following conditions apply:  $V_{IN} = 4\text{ V}$  to  $36\text{ V}$ .

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SWITCHING NODE (SW PIN)</b>						
$t_{ON\_MIN}$	Minimum turn-on time	$I_{OUT} = 600\text{ mA}$		70		ns
$t_{OFF\_MIN}$	Minimum turn-off time	$I_{OUT} = 600\text{ mA}$		100		ns
$t_{ON\_MAX}$	Maximum turn-on time			7.5		$\mu\text{s}$
<b>OSCILLATOR</b>						
$f_{SW}$	Oscillator frequency		0.935	1.1	1.265	MHz

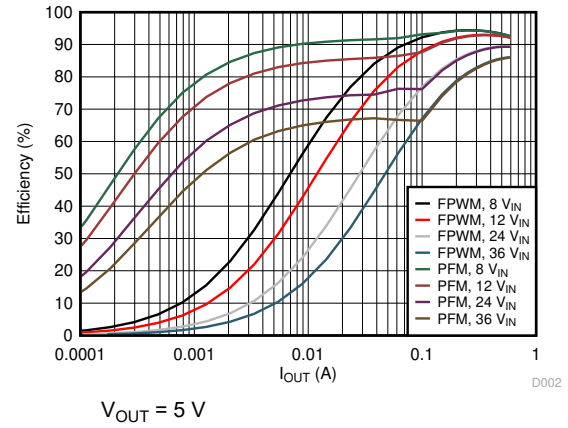
## 7.8 Typical Characteristics

$V_{IN} = 12\text{ V}$ ,  $f_{SW} = 1.1\text{ MHz}$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

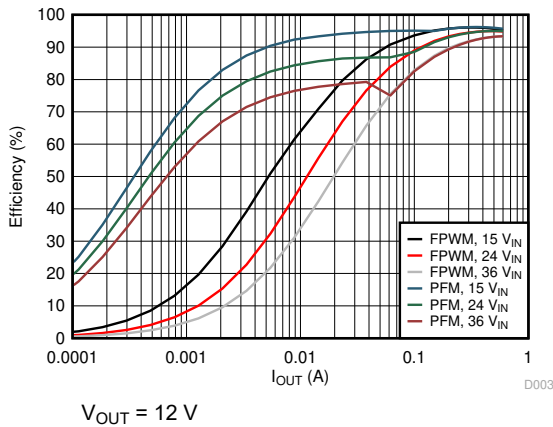
ADVANCE INFORMATION



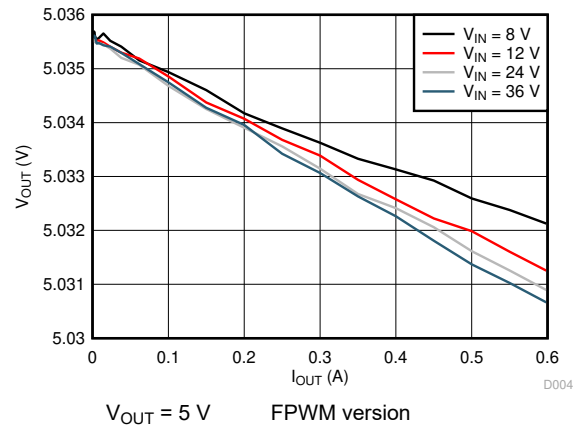
7-1. Efficiency vs Load Current



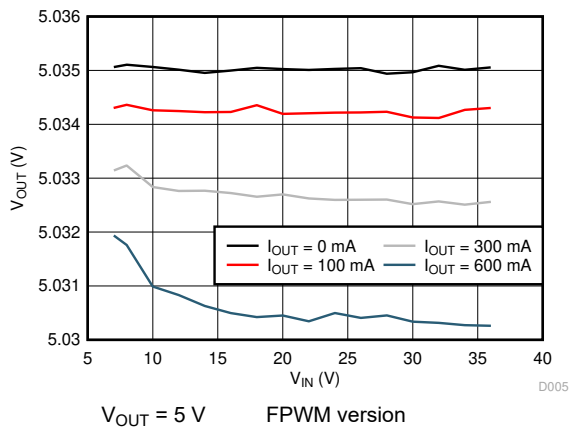
7-2. Efficiency vs Load Current



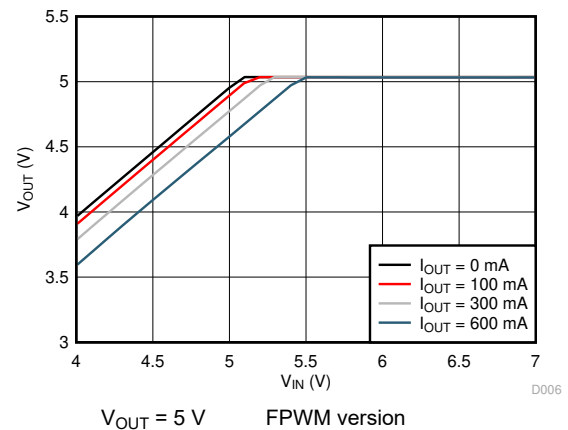
7-3. Efficiency vs Load Current



7-4. Load Regulation



7-5. Line Regulation

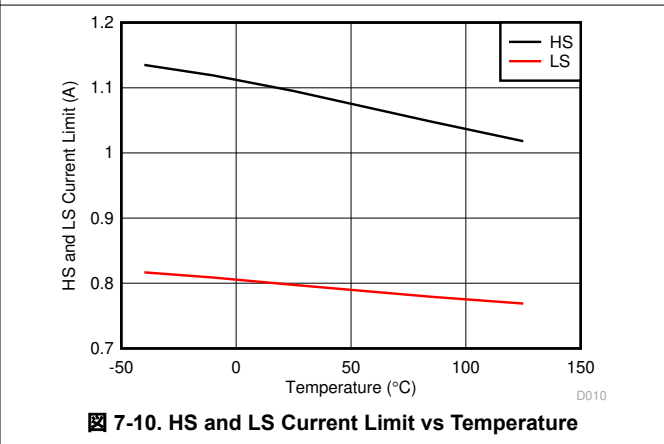
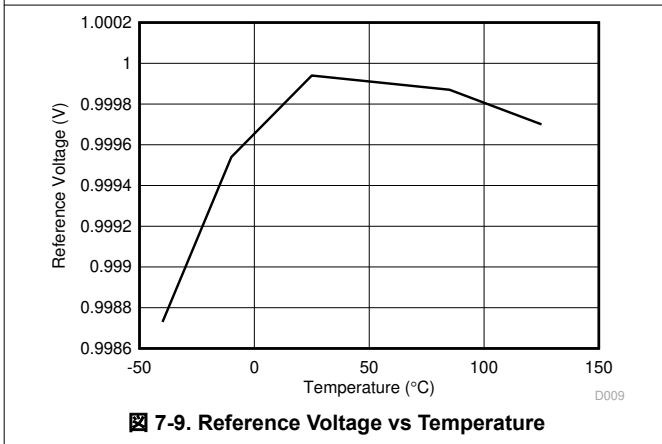
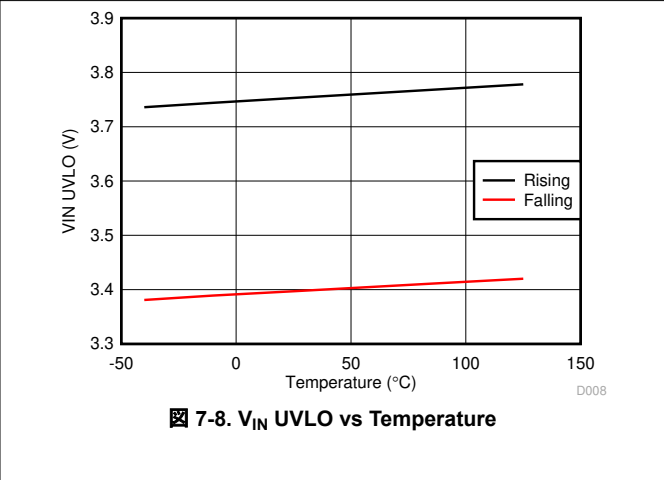
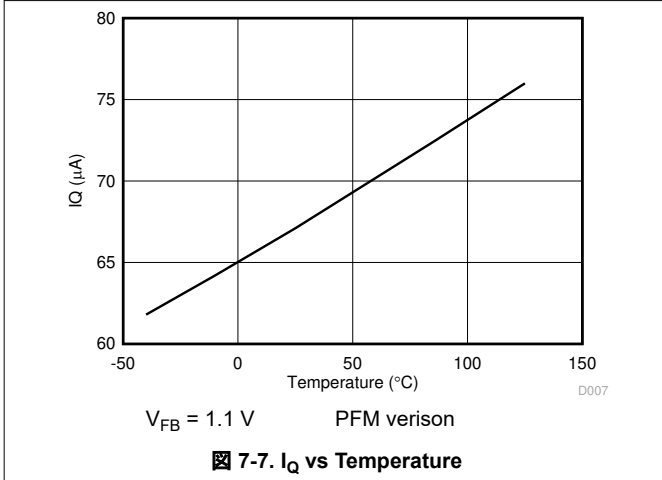


7-6. Dropout



### 7.8 Typical Characteristics (continued)

$V_{IN} = 12\text{ V}$ ,  $f_{SW} = 1.1\text{ MHz}$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise specified.



**ADVANCE INFORMATION**

## 8 Detailed Description

### 8.1 Overview

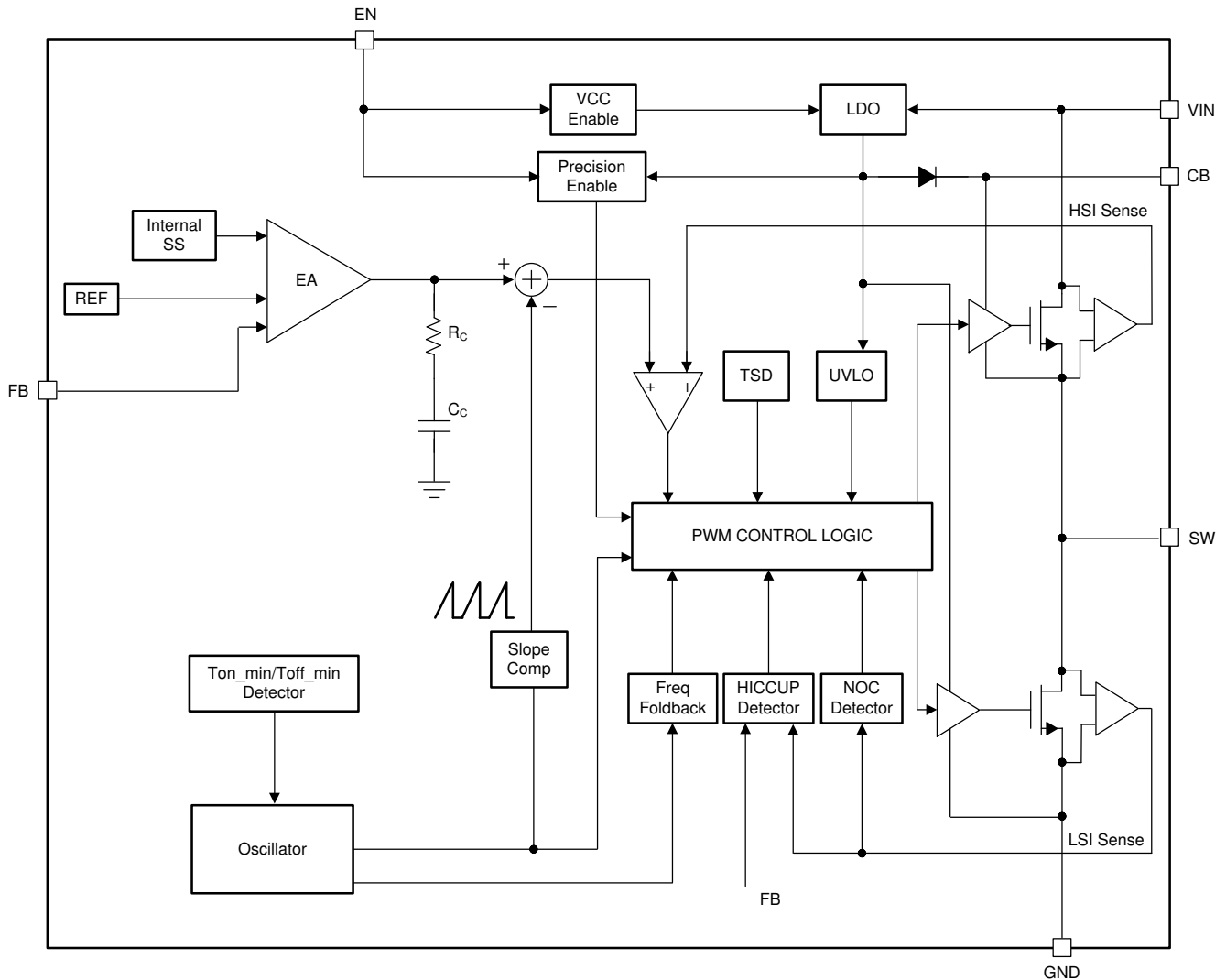
The LV3842 regulator is an easy to use synchronous step-down DC-DC converter operating from 4-V to 36-V supply voltage. The device is capable of delivering up to 600-mA DC load current in a very small solution size.

The LV3842 employs fixed-frequency peak-current mode control. The device enters PFM Mode at light load to achieve high efficiency for PFM version. And FPWM version is provided to achieve low output voltage ripple, tight output voltage regulation, and constant switching frequency at light load. The device is internally compensated, which reduces design time, and requires few external components.

Additional features such as precision enable and internal soft start provide a flexible and easy to use solution for a wide range of applications. Protection features include thermal shutdown,  $V_{IN}$  undervoltage lockout, cycle-by-cycle current limit, and hiccup mode short-circuit protection.

The LV3842 requires very few external components and has a pin-out designed for simple, optimum PCB layout.

### 8.2 Functional Block Diagram



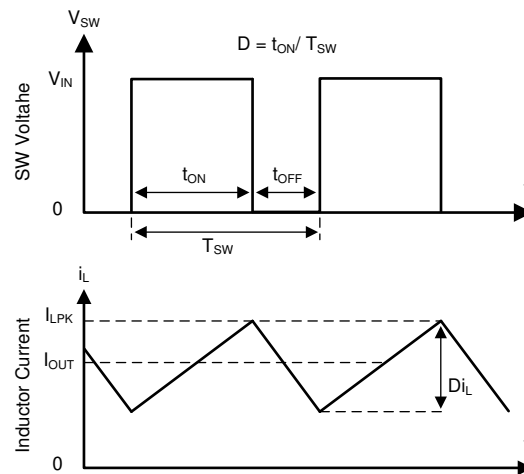
Copyright © 2017, Texas Instruments Incorporated

ADVANCE INFORMATION

## 8.3 Feature Description

### 8.3.1 Fixed Frequency Peak Current Mode Control

The following operation description of the LV3842 will refer to the [セクション 8.2](#) and to the waveforms in [図 8-1](#). LV3842 is a step-down synchronous buck regulator with integrated high-side (HS) and low-side (LS) switches (synchronous rectifier). The LV3842 supplies a regulated output voltage by turning on the HS and LS NMOS switches with controlled duty cycle. During high-side switch ON time, the SW pin voltage swings up to approximately  $V_{IN}$ , and the inductor current  $i_L$  increases with linear slope  $(V_{IN} - V_{OUT}) / L$ . When the HS switch is turned off by the control logic, the LS switch is turned on after an anti-shoot-through dead time. Inductor current discharges through the low-side switch with a slope of  $-V_{OUT} / L$ . The control parameter of a buck converter is defined as Duty Cycle  $D = t_{ON} / T_{SW}$ , where  $t_{ON}$  is the high-side switch ON time and  $T_{SW}$  is the switching period. The regulator control loop maintains a constant output voltage by adjusting the duty cycle  $D$ . In an idea Buck converter, where losses are ignored,  $D$  is proportional to the output voltage and inversely proportional to the input voltage:  $D = V_{OUT} / V_{IN}$ .

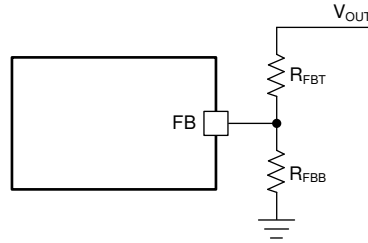


**図 8-1. SW Node and Inductor Current Waveforms in Continuous Conduction Mode (CCM)**

The LV3842 employs fixed-frequency peak-current mode control. A voltage feedback loop is used to get accurate DC voltage regulation by adjusting the peak-current command based on voltage offset. The peak inductor current is sensed from the high-side switch and compared to the peak current threshold to control the ON time of the high-side switch. The voltage feedback loop is internally compensated, which allows for fewer external components, makes it easy to design, and provides stable operation with almost any combination of output capacitors. The regulator operates with fixed switching frequency at normal conditions. At light-load condition, the LV3842 operates in PFM mode to maintain high efficiency (PFM version) or in FPWM mode for low output voltage ripple, tight output voltage regulation, and constant switching frequency (FPWM version).

### 8.3.2 Adjustable Output Voltage

A precision 1.0-V reference voltage  $V_{REF}$  is used to maintain a tightly regulated output voltage over the entire operating temperature range. The output voltage is set by a resistor divider from output voltage to the FB pin. TI recommends to use 1% tolerance resistors with a low temperature coefficient for the FB divider. Select the bottom-side resistor  $R_{FBB}$  for the desired divider current and use [式 1](#) to calculate top-side resistor  $R_{FBT}$ . TI recommends  $R_{FBT}$  in the range from 10 k $\Omega$  to 100 k $\Omega$  for most applications. Lower  $R_{FBT}$  reduces efficiency at very light load. Less static current goes through a larger  $R_{FBT}$  and can be more desirable when light-load efficiency is critical. But TI does not recommend  $R_{FBT}$  larger than 1 M $\Omega$  because it makes the feedback path more susceptible to noise. Larger  $R_{FBT}$  value requires more carefully designed feedback path on the PCB. The tolerance and temperature variation of the resistor dividers affect the output voltage regulation.



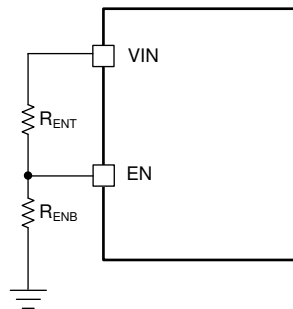
8-2. Output Voltage Setting

$$R_{FBT} = \frac{V_{OUT} - V_{REF}}{V_{REF}} \times R_{FBB} \quad (1)$$

### 8.3.3 Enable

The voltage on the EN pin controls the ON or OFF operation of LV3842. A voltage of less than 0.95 V shuts down the device, while a voltage of more than 1.36 V is required to start the regulator. The EN pin is an input and cannot be left open or floating. The simplest way to enable the operation of the LV3842 is to connect the EN to VIN. This allows self-start-up of the LV3842 when  $V_{IN}$  is within the operating range.

Many applications benefit from the employment of an enable divider  $R_{ENT}$  and  $R_{ENB}$  (8-3) to establish a precision system UVLO level for the converter. System UVLO can be used for supplies operating from utility power as well as battery power. System UVLO can be used for sequencing, ensuring reliable operation, or supply protection, such as a battery discharge level. An external logic signal can also be used to drive EN input for system sequencing and protection. Note that the EN pin voltage must never be higher than  $V_{IN} + 0.3$  V. TI does not recommend to apply EN voltage when  $V_{IN}$  is 0 V.



8-3. System UVLO by Enable Divider

### 8.3.4 Minimum ON-Time, Minimum OFF-Time and Frequency Foldback

Minimum ON-time,  $T_{ON\_MIN}$ , is the smallest duration of time that the HS switch can be on.  $T_{ON\_MIN}$  is typically 70 ns in the LV3842. Minimum OFF-time,  $T_{OFF\_MIN}$ , is the smallest duration that the HS switch can be off.  $T_{OFF\_MIN}$  is typically 100 ns. In CCM operation,  $T_{ON\_MIN}$  and  $T_{OFF\_MIN}$  limit the voltage conversion ratio without switching frequency foldback.

The minimum duty cycle without frequency foldback allowed is

$$D_{MIN} = T_{ON\_MIN} \times f_{SW} \quad (2)$$

The maximum duty cycle without frequency foldback allowed is

$$D_{MAX} = 1 - T_{OFF\_MIN} \times f_{SW} \quad (3)$$

Given a required output voltage, the maximum  $V_{IN}$  without frequency foldback can be found by

$$V_{IN\_MAX} = \frac{V_{OUT}}{f_{SW} \times T_{ON\_MIN}} \quad (4)$$

The minimum  $V_{IN}$  without frequency foldback can be calculated by

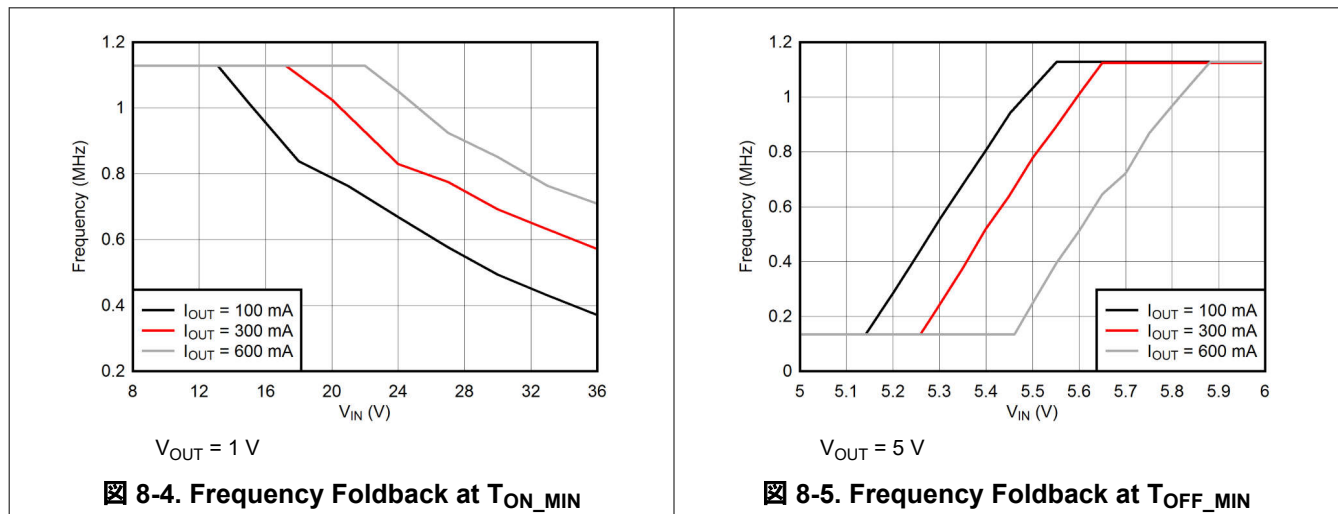
$$V_{IN\_MIN} = \frac{V_{OUT}}{1 - f_{SW} \times T_{OFF\_MIN}} \quad (5)$$

In the LV3842, a frequency foldback scheme is employed after the  $T_{ON\_MIN}$  or  $T_{OFF\_MIN}$  is triggered, which can extend the maximum duty cycle or lower the minimum duty cycle.

The on-time decreases while  $V_{IN}$  voltage increases. After the on-time decreases to  $T_{ON\_MIN}$ , the switching frequency starts to decrease while  $V_{IN}$  continues to go up, which lowers the duty cycle further to keep  $V_{OUT}$  in regulation according to 式 2.

The frequency foldback scheme also works after larger duty cycle is needed under low  $V_{IN}$  conditions. The frequency decreases after the device hits its  $T_{OFF\_MIN}$ , which extends the maximum duty cycle according to 式 3. In such condition, the frequency can be as low as about 133-kHz minimum. Wide range of frequency foldback allows the LV3842 output voltage stay in regulation with a much lower supply voltage  $V_{IN}$ . This leads to a lower effective drop-out voltage.

With frequency foldback,  $V_{IN\_MAX}$  is raised, and  $V_{IN\_MIN}$  is lowered to overcome  $T_{ON\_MIN}$  or  $T_{OFF\_MIN}$  limitation.



### 8.3.5 Bootstrap Voltage

The LV3842 provides an integrated bootstrap voltage regulator. A small capacitor between the CB and SW pins provides the gate drive voltage for the high-side MOSFET. The bootstrap capacitor is refreshed when the high-side MOSFET is off and the low-side switch conducts. The recommended value of the bootstrap capacitor is 0.1  $\mu$ F. TI recommends a ceramic capacitor with an X7R or X5R grade dielectric with a voltage rating of 16 V or higher for stable performance over temperature and voltage.

### 8.3.6 Overcurrent and Short-Circuit Protection

The LV3842 is protected from overcurrent conditions by cycle-by-cycle current limit on both the peak and valley of the inductor current. Hiccup mode is activated if a fault condition persists to prevent over-heating.

High-side MOSFET overcurrent protection is implemented by the nature of the Peak Current Mode control. The HS switch current is sensed when the HS is turned on after a set blanking time. The HS switch current is compared to the output of the Error Amplifier (EA) minus slope compensation every switching cycle. Please refer

to [セクション 8.2](#) for more details. The peak current of HS switch is limited by a clamped maximum peak current threshold  $I_{HS\_LIMIT}$  which is constant.

The current going through LS MOSFET is also sensed and monitored. When the LS switch turns on, the inductor current begins to ramp down. The LS switch is not turned OFF at the end of a switching cycle if its current is above the LS current limit  $I_{LS\_LIMIT}$ . The LS switch is kept ON so that inductor current keeps ramping down, until the inductor current ramps below the LS current limit  $I_{LS\_LIMIT}$ . Then the LS switch is turned OFF and the HS switch is turned on after a dead time. This is somewhat different to the more typical peak current limit, and results in [式 6](#) for the maximum load current.

$$I_{OUT\_MAX} = I_{LS} + \frac{(V_{IN} - V_{OUT})}{2 \times f_{SW} \times L} \times \frac{V_{OUT}}{V_{IN}} \quad (6)$$

If the feedback voltage is lower than 40% of the  $V_{REF}$ , the current of the LS switch triggers LS current limit for 256 consecutive cycles, hiccup current protection mode is activated. In hiccup mode, the regulator shuts down and keeps off for a period of hiccup,  $T_{HICCUP}$  (135-ms typical), before the LV3842 tries to start again. If overcurrent or short-circuit fault condition still exist, hiccup repeats until the fault condition is removed. Hiccup mode reduces power dissipation under severe over-current conditions, prevents over-heating and potential damage to the device.

For FPWM version, the inductor current is allowed to go negative. If this current exceeds the LS negative current limit  $I_{LS\_NEG}$ , the LS switch is turned off and HS switch is turned on immediately. This is used to protect the LS switch from excessive negative current.

### 8.3.7 Soft Start

The integrated soft-start circuit prevents input inrush current impacting the LV3842 and the input power supply. Soft-start is achieved by slowly ramping up the target regulation voltage when the device is first enabled or powered up. The typical soft-start time is 1.8 ms.

The LV3842 also employs over-current protection blanking time  $T_{OCP\_BLK}$  (33 ms typical) at the beginning of power-up. Without this feature, in applications with a large amount of output capacitors and high  $V_{OUT}$ , the inrush current is large enough to trigger the current-limit protection, which can make the device entering into hiccup mode. The device tries to restart after the hiccup period, then hit current-limit and enter into hiccup mode again, so  $V_{OUT}$  cannot ramp up to the setting voltage ever. By introducing OCP blanking feature, the hiccup protection function is disabled during  $T_{OCP\_BLK}$ , and LV3842 charges the  $V_{OUT}$  with its maximum limited current, which maximizes the output current capacity during this period. Kindly note that, the peak current limit ( $I_{HS\_LIMIT}$ ) and valley current limit ( $I_{LS\_LIMIT}$ ) protection function is still available during  $T_{OCP\_BLK}$ , so there is no concern of inductor current running away.

### 8.3.8 Thermal Shutdown

The LV3842 provides an internal thermal shutdown to protect the device when the junction temperature exceeds 170°C. Both HS and LS FETs stop switching in thermal shutdown. After the die temperature falls below 158°C, the device reinitiates the power up sequence controlled by the internal soft-start circuitry.

## 8.4 Device Functional Modes

### 8.4.1 Shutdown Mode

The EN pin provides electrical ON and OFF control for the LV3842. When  $V_{EN}$  is below 0.95 V, the device is in shutdown mode. The LV3842 also employs  $V_{IN}$  under voltage lock out (UVLO) protection. If  $V_{IN}$  voltage is below its UVLO threshold 3.25 V, the regulator is turned off.

### 8.4.2 Active Mode

The LV3842 is in Active Mode when both  $V_{EN}$  and  $V_{IN}$  are above their respective operating threshold. The simplest way to enable the LV3842 is to connect the EN pin to VIN pin. This allows self-startup when the input voltage is in the operating range: 4.0 V to 36 V. Please refer to [セクション 8.3.3](#) section for details on setting these operating levels.

In Active Mode, depending on the load current, the LV3842 will be in one of four modes:

1. Continuous conduction mode (CCM) with fixed switching frequency when load current is above half of the peak-to-peak inductor current ripple (for both PFM and FPWM versions).
2. Discontinuous conduction mode (DCM) with fixed switching frequency when load current is lower than half of the peak-to-peak inductor current ripple in CCM operation (only for PFM version).
3. Pulse frequency modulation mode (PFM) when switching frequency is decreased at very light load (only for PFM version).
4. Forced pulse width modulation mode (FPWM) with fixed switching frequency even at light load (only for FPWM version).

### 8.4.3 CCM Mode

Continuous Conduction Mode (CCM) operation is employed in the LV3842 when the load current is higher than half of the peak-to-peak inductor current. In CCM operation, the frequency of operation is fixed, output voltage ripple is at a minimum in this mode and the maximum output current of 600 mA can be supplied by the LV3842.

### 8.4.4 Light-Load Operation (PFM Version)

For PFM version, when the load current is lower than half of the peak-to-peak inductor current in CCM, the LV3842 operates in Discontinuous Conduction Mode (DCM), also known as Diode Emulation Mode (DEM). In DCM operation, the LS switch is turned off when the inductor current drops to  $I_{LS\_ZC}$  (20 mA typical) to improve efficiency. Both switching losses and conduction losses are reduced in DCM, compared to forced PWM operation at light load.

At even lighter current load, Pulse Frequency Modulation (PFM) mode is activated to maintain high efficiency operation. When either the minimum HS switch ON time  $t_{ON\_MIN}$  or the minimum peak inductor current  $I_{PEAK\_MIN}$  (150mA typical) is reached, the switching frequency decreases to maintain regulation. In PFM mode, switching frequency is decreased by the control loop to maintain output voltage regulation when load current reduces. Switching loss is further reduced in PFM operation due to less frequent switching actions.

### 8.4.5 Light-Load Operation (FPWM Version)

For FPWM version, LV3842 is locked in PWM mode at full load range. This operation is maintained, even in no-load condition, by allowing the inductor current to reverse its normal direction. This mode trades off reduced light load efficiency for low output voltage ripple, tight output voltage regulation, and constant switching frequency.

## 9 Application and Implementation

### 注

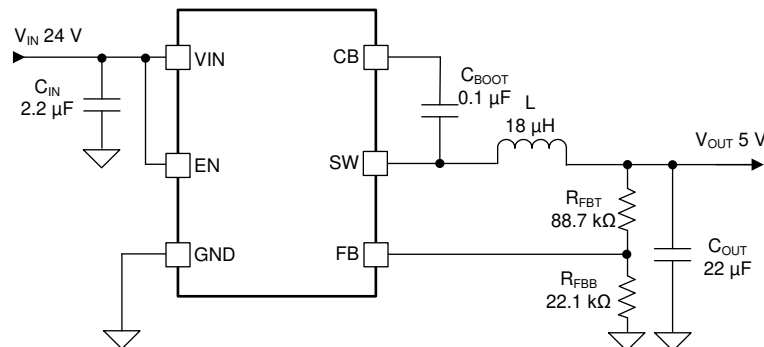
以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくこととなります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

### 9.1 Application Information

The LV3842 is a step down DC-to-DC regulator. The device is typically used to convert a higher DC voltage to a lower DC voltage with a maximum output current of 600 mA. The following design procedure can be used to select components for the LV3842.

### 9.2 Typical Application

The LV3842 only requires a few external components to convert from a wide voltage range supply to a fixed output voltage. [図 9-1](#) shows a basic schematic.



Copyright © 2017, Texas Instruments Incorporated

**図 9-1. Application Circuit**

The external components have to fulfill the needs of the application, but also the stability criteria of the device control loop. [表 9-1](#) can be used to simplify the output filter component selection.

**表 9-1. L and C<sub>OUT</sub> Typical Values**

f <sub>sw</sub> (MHz)	V <sub>OUT</sub> (V)	L (μH)	C <sub>OUT</sub> (μF) <sup>(1)</sup>	R <sub>FBT</sub> (kΩ)	R <sub>FBB</sub> (kΩ)
1.1	3.3	12	22 μF / 10 V	51	22.1
	5	18	22 μF / 10 V	88.7	22.1
	12	33	10 μF / 25 V	243	22.1

(1) Ceramic capacitor is used in this table.



## 9.2.1 Design Requirements

Detailed design procedure is described based on a design example. For this design example, use the parameters listed in 表 9-2 as the input parameters.

表 9-2. Design Example Parameters

PARAMETER	VALUE
Input voltage, $V_{IN}$	12 V typical, range from 6 V to 36 V
Output voltage, $V_{OUT}$	5 V $\pm$ 3%
Maximum output current, $I_{OUT\_MAX}$	600 mA
Minimum output current, $I_{OUT\_MIN}$	30 mA
Output overshoot/ undershoot (0mA to 600mA )	5%
Output voltage ripple	0.5%
Operating frequency	1.1 MHz

## 9.2.2 Detailed Design Procedure

### 9.2.2.1 Output Voltage Set-Point

The output voltage of the LV3842 device is externally adjustable using a resistor divider network. The divider network is comprised of top feedback resistor  $R_{FBT}$  and bottom feedback resistor  $R_{FBB}$ . 式 7 is used to determine the output voltage of the converter:

$$R_{FBT} = \frac{V_{OUT} - V_{REF}}{V_{REF}} \times R_{FBB} \quad (7)$$

Choose the value of  $R_{FBB}$  to be 22.1 k $\Omega$ . With the desired output voltage set to 5 V and the  $V_{REF} = 1.0$  V, the  $R_{FBT}$  value can then be calculated using 式 7. The formula yields to a value 88.4 k $\Omega$ , a standard value of 88.7 k $\Omega$  is selected.

### 9.2.2.2 Inductor Selection

The most critical parameters for the inductor are the inductance, saturation current and the RMS current. The inductance is based on the desired peak-to-peak ripple current  $\Delta i_L$ . Because the ripple current increases with the input voltage, the maximum input voltage is always used to calculate the minimum inductance  $L_{MIN}$ . Use 式 9 to calculate the minimum value of the output inductor.  $K_{IND}$  is a coefficient that represents the amount of inductor ripple current relative to the maximum output current of the device. A reasonable value of  $K_{IND}$  must be 20% – 40%. During an instantaneous over current operation event, the RMS and peak inductor current can be high. The inductor current rating must be a bit higher than current limit.

$$\Delta i_L = \frac{V_{OUT} \times (V_{IN\_MAX} - V_{OUT})}{V_{IN\_MAX} \times L \times f_{SW}} \quad (8)$$

$$L_{MIN} = \frac{V_{IN\_MAX} - V_{OUT}}{I_{OUT} \times K_{IND}} \times \frac{V_{OUT}}{V_{IN\_MAX} \times f_{SW}} \quad (9)$$

In general, it is preferable to choose lower inductance in switching power supplies, because it usually corresponds to faster transient response, smaller DCR, and reduced size for more compact designs. But too low of an inductance can generate too large of an inductor current ripple such that over current protection at the full load can be falsely triggered. It also generates more inductor core loss because the current ripple is larger. Larger inductor current ripple also implies larger output voltage ripple with same output capacitors. With peak current mode control, TI does not recommend to have too small of an inductor current ripple. A larger peak current ripple improves the comparator signal to noise ratio.

For this design example, choose  $K_{IND} = 0.4$ , the minimum inductor value is calculated to be 16.3  $\mu$ H. Choose the nearest standard 18  $\mu$ H ferrite inductor with a capability of 1 A RMS current and 1.5 A saturation current.

### 9.2.2.3 Output Capacitor Selection

The device is designed to be used with a wide variety of LC filters. It is generally desired to use as little output capacitance as possible to keep cost and size down. The output capacitors,  $C_{OUT}$ , must be chosen with care because it directly affects the steady state output voltage ripple, loop stability and the voltage over/undershoot during load current transients. The output voltage ripple is essentially composed of two parts. One is caused by the inductor current ripple going through the Equivalent Series Resistance (ESR) of the output capacitors:

$$\Delta V_{OUT\_ESR} = \Delta i_L \times ESR = K_{IND} \times I_{OUT} \times ESR \quad (10)$$

The other is caused by the inductor current ripple charging and discharging the output capacitors:

$$\Delta V_{OUT\_C} = \frac{\Delta i_L}{8 \times f_{SW} \times C_{OUT}} = \frac{K_{IND} \times I_{OUT}}{8 \times f_{SW} \times C_{OUT}} \quad (11)$$

The two components in the voltage ripple are not in phase, so the actual peak-to-peak ripple is smaller than the sum of the two peaks.

Output capacitance is usually limited by transient performance specifications if the system requires tight voltage regulation with presence of large current steps and fast slew rate. When a large load step happens, output capacitors provide the required charge before the inductor current can slew up to the appropriate level. The regulator control loop usually needs 8 or more clock cycles to regulate the inductor current equal to the new load level. The output capacitance must be large enough to supply the current difference for 8 clock cycles to maintain the output voltage within the specified range. 式 12 shows the minimum output capacitance needed for specified output over/undershoot.

$$C_{OUT} > \frac{1}{2} \times \frac{8 \times (I_{OH} - I_{OL})}{f_{SW} \times \Delta V_{OUT\_SHOOT}} \quad (12)$$

where

- $K_{IND}$  = Ripple ratio of the inductor ripple current ( $\Delta i_L / I_{OUT}$ )
- $I_{OL}$  = Low level output current during load transient
- $I_{OH}$  = High level output current during load transient
- $V_{OUT\_SHOOT}$  = Target output voltage over/undershoot

For this design example, the target output ripple is 30 mV. Presuppose  $\Delta V_{OUT\_ESR} = \Delta V_{OUT\_C} = 30$  mV, and chose  $K_{IND} = 0.4$ . 式 10 yields ESR no larger than 125 mΩ and 式 11 yields  $C_{OUT}$  no smaller than 0.91 μF. For the target over/undershoot range of this design,  $\Delta V_{OUT\_SHOOT} = 5\% \times V_{OUT} = 250$  mV. The  $C_{OUT}$  can be calculated to be no smaller than 8.3 μF by 式 12. In summary, the most stringent criteria for the output capacitor is 8.3 μF. Consider of derating, one 22 μF, 10 V, X7R ceramic capacitor with 10 mΩ ESR is used.

### 9.2.2.4 Input Capacitor Selection

The LV3842 device requires high frequency input decoupling capacitors and a bulk input capacitor, depending on the application. The typical recommended value for the high frequency decoupling capacitor is 2.2 μF or higher. TI recommends a high-quality ceramic type X5R or X7R with sufficiency voltage rating. The voltage rating must be greater than the maximum input voltage. To compensate the derating of ceramic capacitors, TI recommends a voltage rating of twice the maximum input voltage. Additionally, some bulk capacitance can be required, especially if the LV3842 circuit is not located within approximately 5 cm from the input voltage source. This capacitor is used to provide damping to the voltage spiking due to the lead inductance of the cable or trace. The value for this capacitor is not critical but must be rated to handle the maximum input voltage including ripple. For this design, one 2.2 μF, X7R dielectric capacitor rated for 50 V is used for the input decoupling capacitor. The equivalent series resistance (ESR) is approximately 10 mΩ, and the current rating is 1 A. Include a capacitor with a value of 0.1 μF for high-frequency filtering and place it as close as possible to the device pins.

### 9.2.2.5 Bootstrap Capacitor

Every LV3842 design requires a bootstrap capacitor,  $C_{BOOT}$ . The recommended bootstrap capacitor is 0.1  $\mu\text{F}$  and rated at 16 V or higher. The bootstrap capacitor is located between the SW pin and the CB pin. The bootstrap capacitor must be a high-quality ceramic type with X7R or X5R grade dielectric for temperature stability.

### 9.2.2.6 Undervoltage Lockout Set-Point

The system undervoltage lockout (UVLO) is adjusted using the external voltage divider network of  $R_{ENT}$  and  $R_{ENB}$ . The UVLO has two thresholds, one for power up when the input voltage is rising and one for power down or brown outs when the input voltage is falling. The following equation can be used to determine the  $V_{IN}$  UVLO level.

$$V_{IN\_RISING} = V_{ENH} \times \frac{R_{ENT} + R_{ENB}}{R_{ENB}} \quad (13)$$

The EN rising threshold ( $V_{ENH}$ ) for LV3842 is set to be 1.23 V (typical). Choose the value of  $R_{ENB}$  to be 200 k $\Omega$  to minimize input current from the supply. If the desired  $V_{IN}$  UVLO level is at 6.0 V, then the value of  $R_{ENT}$  can be calculated using 式 14:

$$R_{ENT} = \left( \frac{V_{IN\_RISING}}{V_{ENH}} - 1 \right) \times R_{ENB} \quad (14)$$

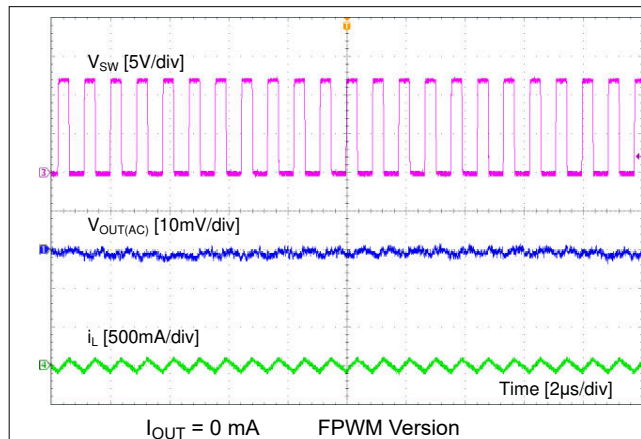
The above equation yields a value of 775.6 k $\Omega$ , a standard value of 768 k $\Omega$  is selected. The resulting falling UVLO threshold, equals 5.3 V, can be calculated by 式 15, where EN hysteresis ( $V_{EN\_HYS}$ ) is 0.13 V (typical).

$$V_{IN\_FALLING} = (V_{ENH} - V_{EN\_HYS}) \times \frac{R_{ENT} + R_{ENB}}{R_{ENB}} \quad (15)$$

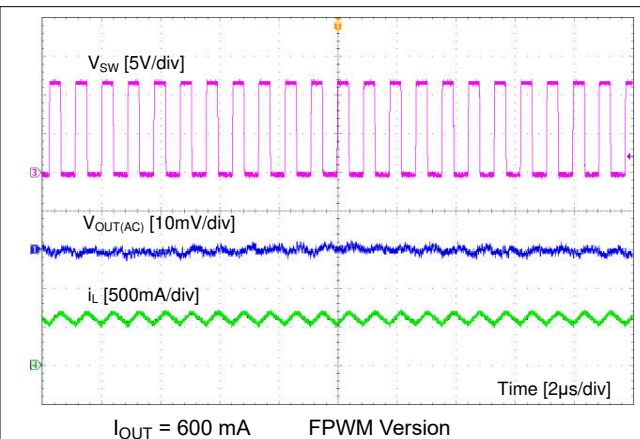
### 9.2.3 Application Curves

Unless otherwise specified the following conditions apply:  $V_{IN} = 12\text{ V}$ ,  $V_{OUT} = 5\text{ V}$ ,  $f_{SW} = 1.1\text{ MHz}$ ,  $L = 18\text{ }\mu\text{H}$ ,  $C_{OUT} = 22\text{ }\mu\text{F}$ ,  $T_A = 25\text{ }^\circ\text{C}$

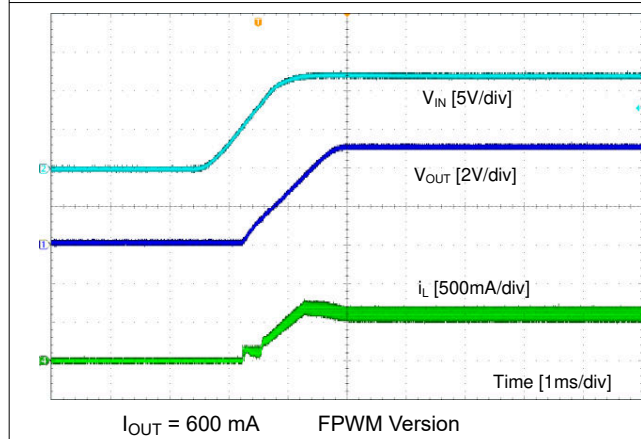
ADVANCE INFORMATION



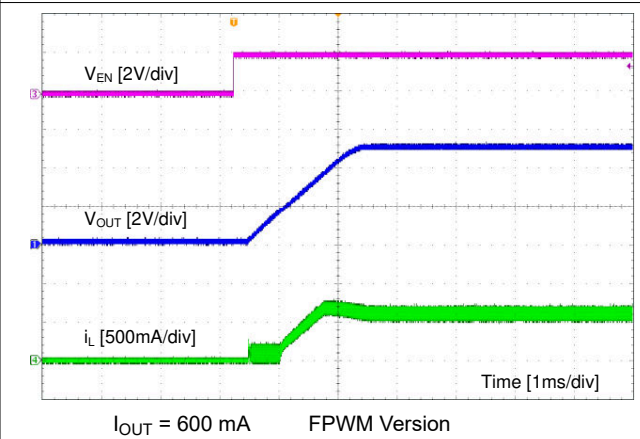
9-2. Ripple at No Load



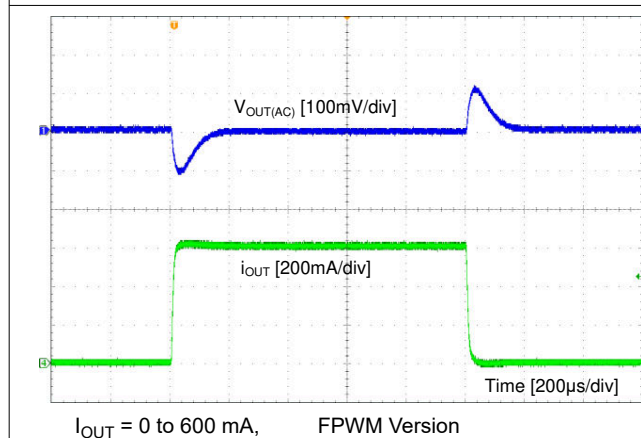
9-3. Ripple at Full Load



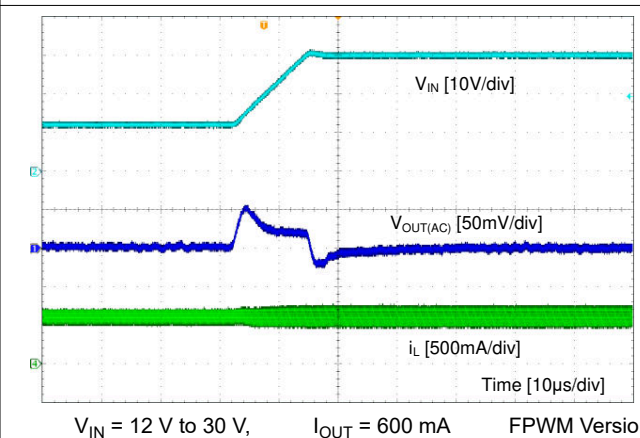
9-4. Start-up by  $V_{IN}$



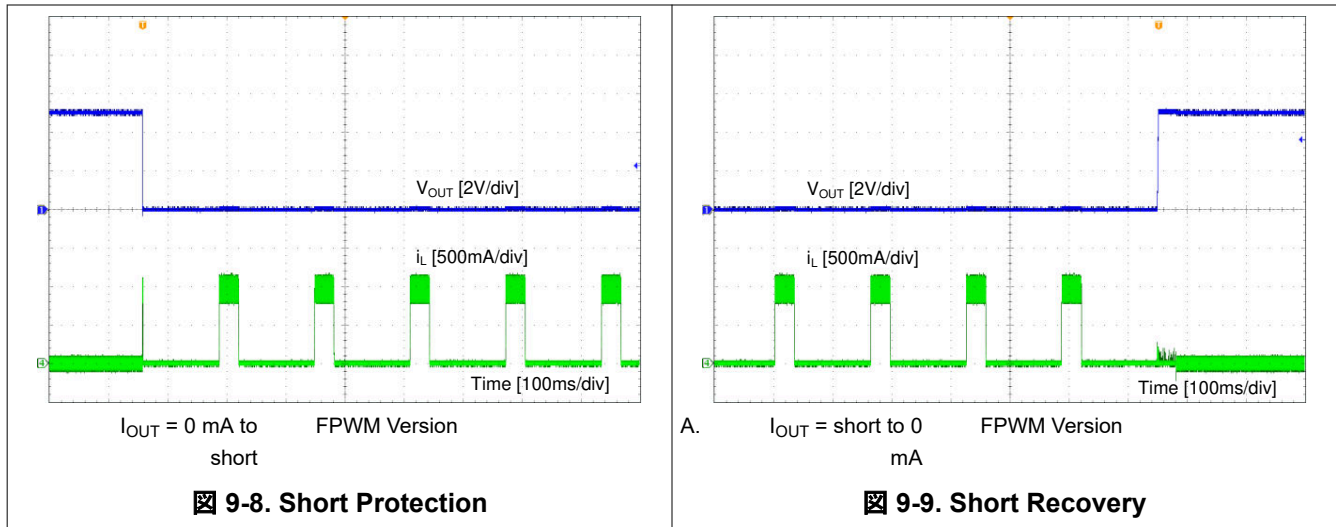
9-5. Start-up by EN



9-6. Load Transient



9-7. Line Transient



### 9.3 Power Supply Recommendations

The LV3842 is designed to operate from an input voltage supply range between 4.0 V and 36 V. This input supply must be well regulated and able to withstand maximum input current and maintain a stable voltage. The resistance of the input supply rail must be low enough that an input current transient does not cause a high enough drop at the LV3842 supply voltage that can cause a false UVLO fault triggering and system reset. If the input supply is located more than a few inches from the LV3842 additional bulk capacitance can be required in addition to the ceramic bypass capacitors. The amount of bulk capacitance is not critical, but a 10  $\mu$ F or 22  $\mu$ F electrolytic capacitor is a typical choice.

### 9.4 Layout

#### 9.4.1 Layout Guidelines

Layout is a critical portion of good power supply design. The following guidelines will help users design a PCB with the best power conversion performance, thermal performance, and minimized generation of unwanted EMI.

1. The input bypass capacitor  $C_{IN}$  must be placed as close as possible to the VIN and GND pins. Grounding for both the input and output capacitors must consist of localized top side planes that connect to the GND pin.
2. Minimize trace length to the FB pin net. Both feedback resistors,  $R_{FBT}$  and  $R_{FBB}$  must be located close to the FB pin. If  $V_{OUT}$  accuracy at the load is important, make sure  $V_{OUT}$  sense is made at the load. Route  $V_{OUT}$  sense path away from noisy nodes and preferably through a layer on the other side of a shielded layer.
3. Use ground plane in one of the middle layers as noise shielding and heat dissipation path if possible.
4. Make  $V_{IN}$ ,  $V_{OUT}$  and ground bus connections as wide as possible. This reduces any voltage drops on the input or output paths of the converter and maximizes efficiency.
5. Provide adequate device heat-sinking. GND, VIN and SW pins provide the main heat dissipation path, make the GND, VIN and SW plane area as large as possible. Use an array of heat-sinking vias to connect the top side ground plane to the ground plane on the bottom PCB layer. If the PCB has multiple copper layers, these thermal vias can also be connected to inner layer heat-spreading ground planes. Ensure enough copper area is used for heat-sinking to keep the junction temperature below 125 °C.

#### 9.4.2 Compact Layout for EMI Reduction

Radiated EMI is generated by the high di/dt components in pulsing currents in switching converters. The larger area covered by the path of a pulsing current, the more EMI is generated. High frequency ceramic bypass capacitors at the input side provide primary path for the high di/dt components of the pulsing current. Placing ceramic bypass capacitors as close as possible to the VIN and GND pins is the key to EMI reduction.

The SW pin connecting to the inductor must be as short as possible, and just wide enough to carry the load current without excessive heating. Short, thick traces or copper pours (shapes) must be used for high current

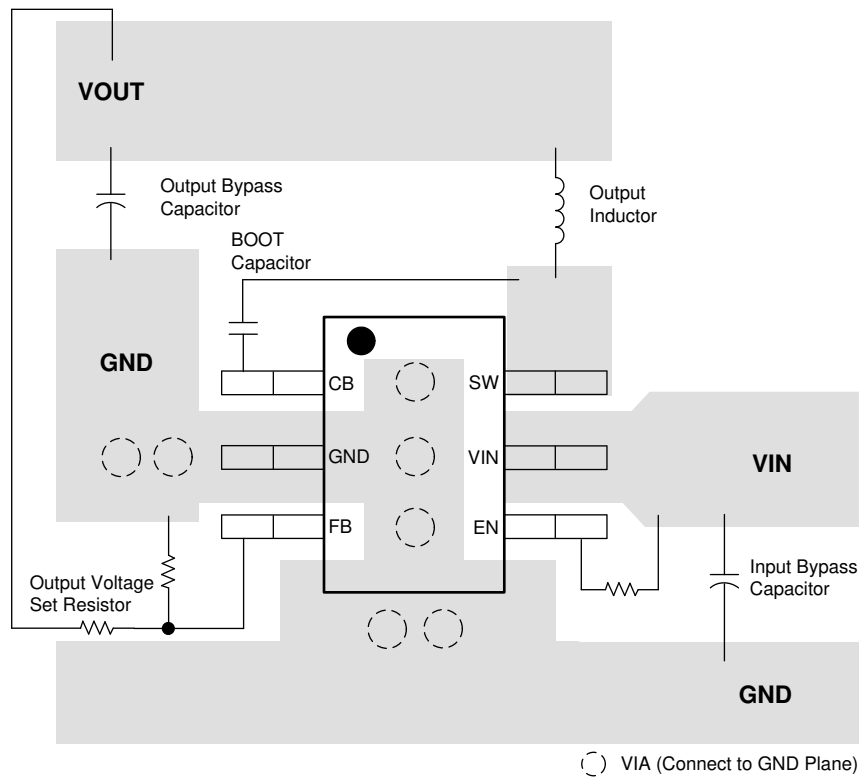
conduction path to minimize parasitic resistance. The output capacitors must be placed close to the  $V_{OUT}$  end of the inductor and closely grounded to GND pin.

### 9.4.3 Feedback Resistors

To reduce noise sensitivity of the output voltage feedback path, it is important to place the resistor divider close to the FB pin, rather than close to the load. The FB pin is the input to the error amplifier, so it is a high impedance node and very sensitive to noise. Placing the resistor divider closer to the FB pin reduces the trace length of FB signal and reduces noise coupling. The output node is a low impedance node, so the trace from  $V_{OUT}$  to the resistor divider can be long if short path is not available.

If voltage accuracy at the load is important, make sure voltage sense is made at the load. Doing so will correct for voltage drops along the traces and provide the best output accuracy. The voltage sense trace from the load to the feedback resistor divider must be routed away from the SW node path and the inductor to avoid contaminating the feedback signal with switch noise, while also minimizing the trace length. This is most important when high value resistors are used to set the output voltage. TI recommends to route the voltage sense trace and place the resistor divider on a different layer than the inductor and SW node path, such that there is a ground plane in between the feedback trace and inductor/SW node polygon. This provides further shielding for the voltage feedback path from EMI noises.

### 9.4.4 Layout Example



9-10. Layout

## 10 Device and Documentation Support

### 10.1 Documentation Support

#### 10.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [AN-1149 Layout Guidelines for Switching Power Supplies application report](#)

### 10.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、[ti.com](#) のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

### 10.3 サポート・リソース

[TI E2E™ サポート・フォーラム](#)は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するものではなく、必ずしも TI の見解を反映したものではありません。TI の[使用条件](#)を参照してください。

### 10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

### 10.5 静電気放電に関する注意事項



この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

### 10.6 用語集

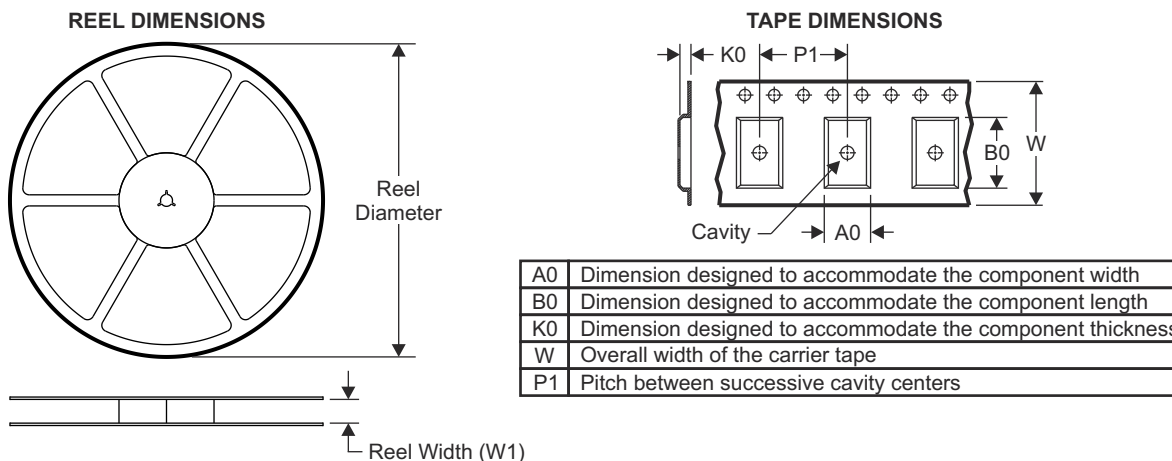
[テキサス・インスツルメンツ用語集](#)

この用語集には、用語や略語の一覧および定義が記載されています。

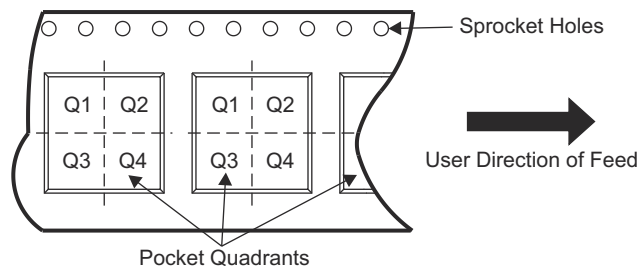
## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

### 11.1 Tape and Reel Information



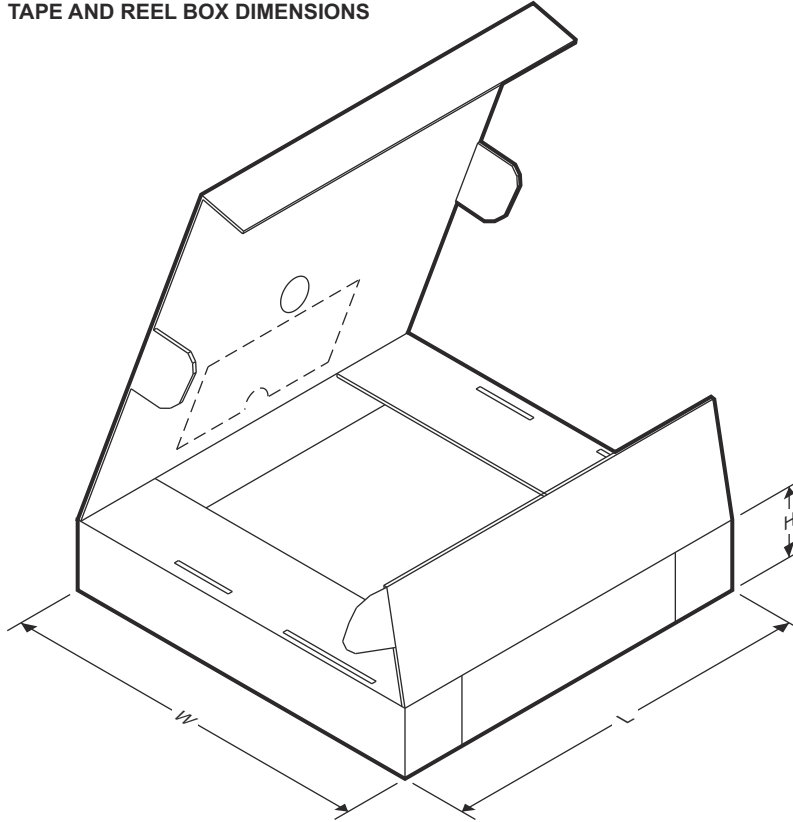
#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LV3842XFDBVT	SOT-23	DBV	6	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LV3842XFDBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LV3842XDBVT	SOT-23	DBV	6	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LV3842XDBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3



**TAPE AND REEL BOX DIMENSIONS**

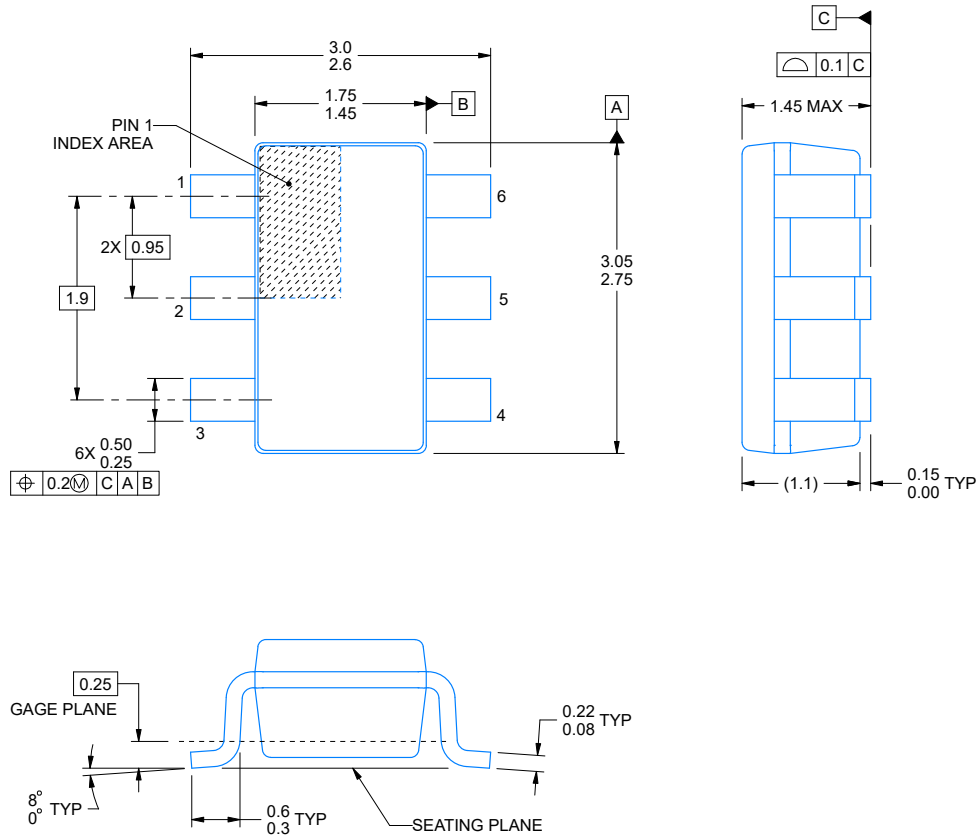


Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LV3842XFDBVT	SOT-23	DBV	6	250	210.0	185.0	35.0
LV3842XFDBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
LV3842XDBVT	SOT-23	DBV	6	250	210.0	185.0	35.0
LV3842XDBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0

**ADVANCE INFORMATION**

**DBV0006A****PACKAGE OUTLINE****SOT-23 - 1.45 mm max height**

SMALL OUTLINE TRANSISTOR



4214840/C 06/2021

**NOTES:**

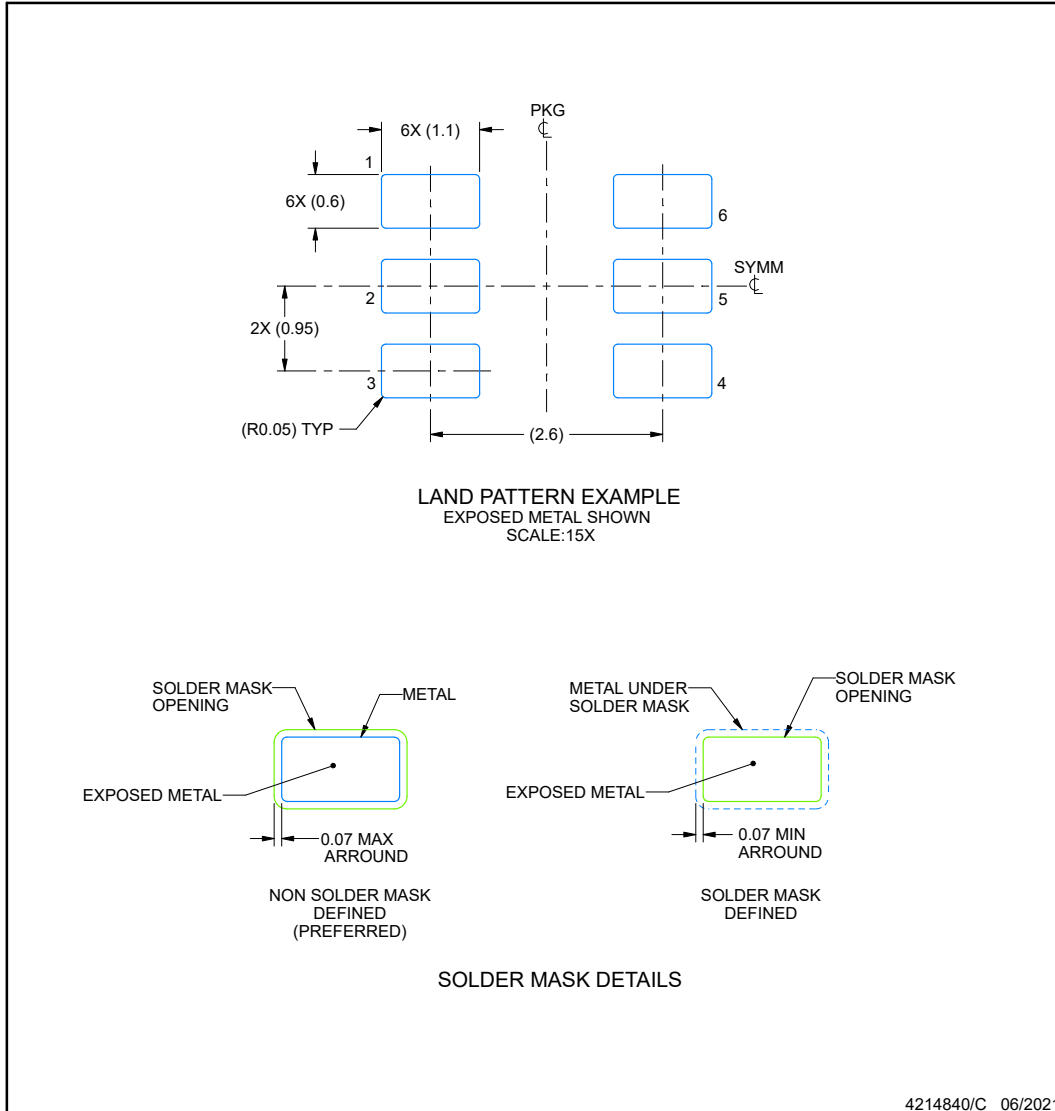
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Reference JEDEC MO-178.

## EXAMPLE BOARD LAYOUT

**DBV0006A**

**SOT-23 - 1.45 mm max height**

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

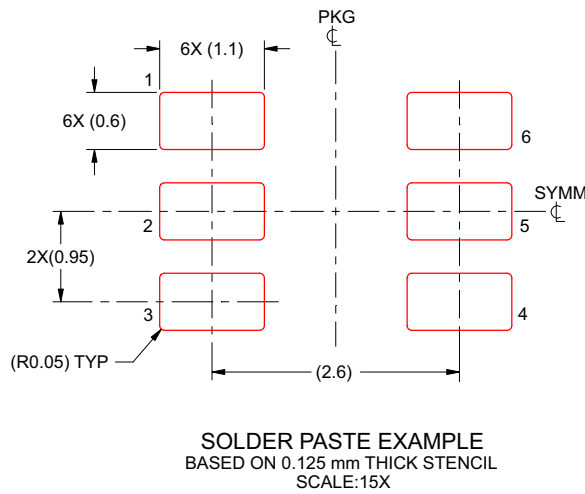
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

**EXAMPLE STENCIL DESIGN**

**DBV0006A**

**SOT-23 - 1.45 mm max height**

SMALL OUTLINE TRANSISTOR



4214840/C 06/2021

NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.

**ADVANCE INFORMATION**

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LV3842XDBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	1S1F	<a href="#">Samples</a>
LV3842XFDBVR	ACTIVE	SOT-23	DBV	6	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	VAXF	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



# DBV0006A



# PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



4214840/G 08/2024

## NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.
4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
5. Reference JEDEC MO-178.

# EXAMPLE BOARD LAYOUT

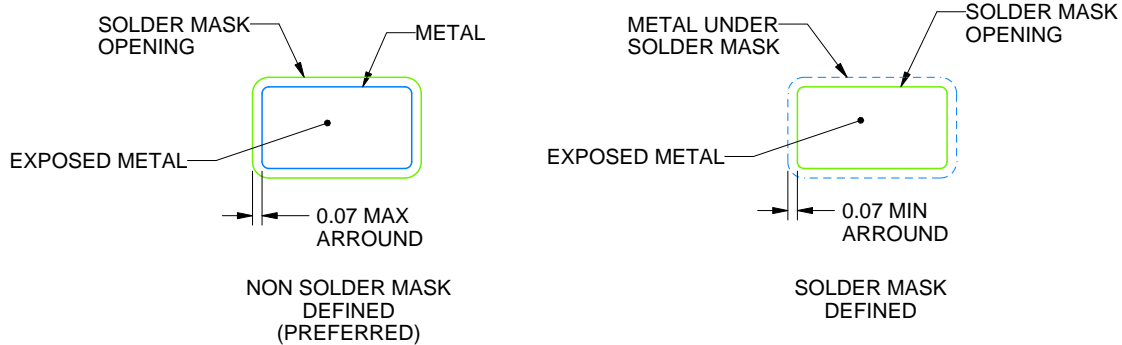
DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4214840/G 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# EXAMPLE STENCIL DESIGN

DBV0006A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

4214840/G 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## 重要なお知らせと免責事項

TI は、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス・デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、TI 製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した TI 製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとし、

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている TI 製品を使用するアプリケーションの開発の目的でのみ、TI はその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。TI や第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、TI およびその代理人を完全に補償するものとし、TI は一切の責任を拒否します。

TI の製品は、[TI の販売条件](#)、または [ti.com](#) やかかる TI 製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。TI がこれらのリソースを提供することは、適用される TI の保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、TI はそれらに異議を唱え、拒否します。

郵送先住所 : Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
Copyright © 2024, Texas Instruments Incorporated